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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	20MHz
Connectivity	-
Peripherals	POR, WDT
Number of I/O	20
Program Memory Size	3KB (2K x 12)
Program Memory Type	OTP
EEPROM Size	-
RAM Size	72 x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	-
Oscillator Type	External
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Through Hole
Package / Case	28-DIP (0.600", 15.24mm)
Supplier Device Package	28-PDIP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16c57-hsi-p

TABLE 3-1: PINOUT DESCRIPTION - PIC16C54, PIC16CR54, PIC16C56, PIC16CR56, PIC16C58, PIC16CR58

Pin Name	Pin Number			Pin Type	Buffer Type	Description
	DIP	SOIC	SSOP			
RA0	17	17	19	I/O	TTL	Bi-directional I/O port
RA1	18	18	20	I/O	TTL	
RA2	1	1	1	I/O	TTL	
RA3	2	2	2	I/O	TTL	
RB0	6	6	7	I/O	TTL	Bi-directional I/O port
RB1	7	7	8	I/O	TTL	
RB2	8	8	9	I/O	TTL	
RB3	9	9	10	I/O	TTL	
RB4	10	10	11	I/O	TTL	
RB5	11	11	12	I/O	TTL	
RB6	12	12	13	I/O	TTL	
RB7	13	13	14	I/O	TTL	
T0CKI	3	3	3	I	ST	Clock input to Timer0. Must be tied to V_{SS} or V_{DD}, if not in use, to reduce current consumption.
$\overline{MCLR}/V_{PP}$	4	4	4	I	ST	Master clear (RESET) input/programming voltage input. This pin is an active low RESET to the device. Voltage on the $\overline{MCLR}/V_{PP}$ pin must not exceed V_{DD} to avoid unintended entering of Programming mode.
OSC1/CLKIN	16	16	18	I	ST	Oscillator crystal input/external clock source input.
OSC2/CLKOUT	15	15	17	O	—	Oscillator crystal output. Connects to crystal or resonator in crystal Oscillator mode. In RC mode, OSC2 pin outputs CLKOUT, which has 1/4 the frequency of OSC1 and denotes the instruction cycle rate.
V_{DD}	14	14	15,16	P	—	Positive supply for logic and I/O pins.
V_{SS}	5	5	5,6	P	—	Ground reference for logic and I/O pins.

Legend: I = input, O = output, I/O = input/output, P = power, — = Not Used, TTL = TTL input, ST = Schmitt Trigger input

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4.0 OSCILLATOR CONFIGURATIONS

4.1 Oscillator Types

PIC16C5Xs can be operated in four different oscillator modes. The user can program two configuration bits (FOSC1:FOSC0) to select one of these four modes:

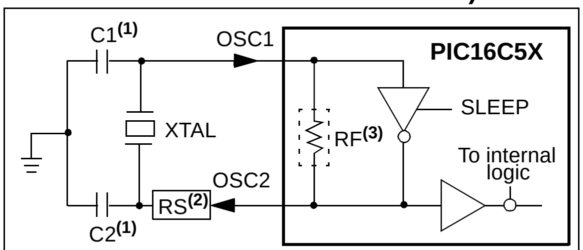
1. LP: Low Power Crystal
2. XT: Crystal/Resonator
3. HS: High Speed Crystal/Resonator
4. RC: Resistor/Capacitor

Note:	Not all oscillator selections available for all parts. See Section 9.1.

4.2 Crystal Oscillator/Ceramic Resonators

In XT, LP or HS modes, a crystal or ceramic resonator is connected to the OSC1/CLKIN and OSC2/CLKOUT pins to establish oscillation (Figure 4-1). The PIC16C5X oscillator design requires the use of a parallel cut crystal. Use of a series cut crystal may give a frequency out of the crystal manufacturers specifications. When in XT, LP or HS modes, the device can have an external clock source drive the OSC1/CLKIN pin (Figure 4-2).

FIGURE 4-1: CRYSTAL/CERAMIC RESONATOR OPERATION (HS, XT OR LP OSC CONFIGURATION)



Note 1: See Capacitor Selection tables for recommended values of C1 and C2.

2: A series resistor (RS) may be required for AT strip cut crystals.

3: RF varies with the Oscillator mode chosen (approx. value = 10 MΩ).

FIGURE 4-2: EXTERNAL CLOCK INPUT OPERATION (HS, XT OR LP OSC CONFIGURATION)

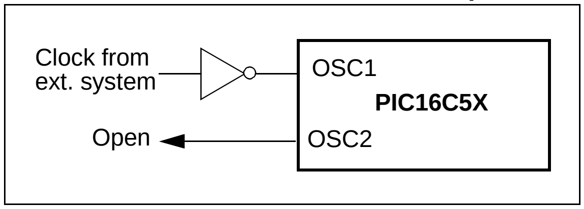


TABLE 4-1: CAPACITOR SELECTION FOR CERAMIC RESONATORS - PIC16C5X, PIC16CR5X

Osc Type	Resonator Freq	Cap. Range C1	Cap. Range C2
XT	455 kHz 2.0 MHz 4.0 MHz	68-100 pF 15-33 pF 10-22 pF	68-100 pF 15-33 pF 10-22 pF
HS	8.0 MHz 16.0 MHz	10-22 pF 10 pF	10-22 pF 10 pF

These values are for design guidance only. Since each resonator has its own characteristics, the user should consult the resonator manufacturer for appropriate values of external components.

TABLE 4-2: CAPACITOR SELECTION FOR CRYSTAL OSCILLATOR - PIC16C5X, PIC16CR5X

Osc Type	Crystal Freq	Cap.Range C1	Cap. Range C2
LP	32 kHz(1)	15 pF	15 pF
XT	100 kHz 200 kHz 455 kHz 1 MHz 2 MHz 4 MHz	15-30 pF 15-30 pF 15-30 pF 15-30 pF 15 pF 15 pF	200-300 pF 100-200 pF 15-100 pF 15-30 pF 15 pF 15 pF
HS	4 MHz 8 MHz 20 MHz	15 pF 15 pF 15 pF	15 pF 15 pF 15 pF

Note 1: For V_{DD} > 4.5V, C1 = C2 ≈ 30 pF is recommended.

These values are for design guidance only. Rs may be required in HS mode as well as XT mode to avoid overdriving crystals with low drive level specification. Since each crystal has its own characteristics, the user should consult the crystal manufacturer for appropriate values of external components.

Note:	If you change from this device to another device, please verify oscillator characteristics in your application.

4.3 External Crystal Oscillator Circuit

Either a prepackaged oscillator or a simple oscillator circuit with TTL gates can be used as an external crystal oscillator circuit. Prepackaged oscillators provide a wide operating range and better stability. A well-designed crystal oscillator will provide good performance with TTL gates. Two types of crystal oscillator circuits can be used: one with parallel resonance, or one with series resonance.

Figure 4-3 shows an implementation example of a parallel resonant oscillator circuit. The circuit is designed to use the fundamental frequency of the crystal. The 74AS04 inverter performs the 180-degree phase shift that a parallel oscillator requires. The 4.7 kΩ resistor provides the negative feedback for stability. The 10 kΩ potentiometers bias the 74AS04 in the linear region. This circuit could be used for external oscillator designs.

FIGURE 4-3: EXAMPLE OF EXTERNAL PARALLEL RESONANT CRYSTAL OSCILLATOR CIRCUIT (USING XT, HS OR LP OSCILLATOR MODE)

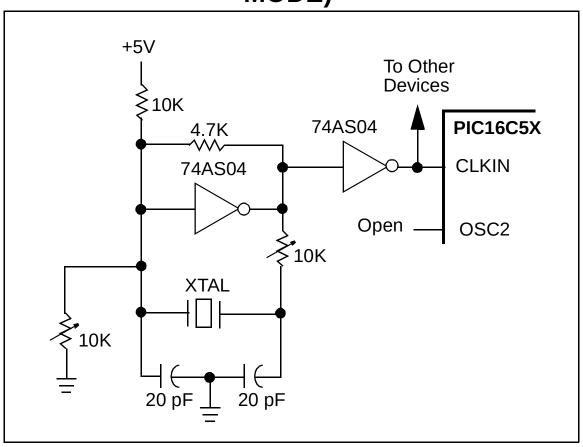
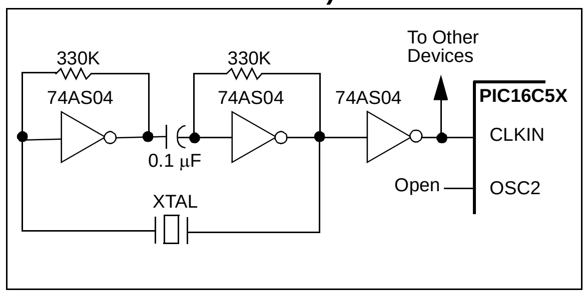


Figure 4-4 shows a series resonant oscillator circuit. This circuit is also designed to use the fundamental frequency of the crystal. The inverter performs a 180-degree phase shift in a series resonant oscillator circuit. The 330 kΩ resistors provide the negative feedback to bias the inverters in their linear region.

FIGURE 4-4: EXAMPLE OF EXTERNAL SERIES RESONANT CRYSTAL OSCILLATOR CIRCUIT (USING XT, HS OR LP OSCILLATOR MODE)



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7.0 I/O PORTS

As with any other register, the I/O Registers can be written and read under program control. However, read instructions (e.g., `MOVF PORTB,W`) always read the I/O pins independent of the pin's input/output modes. On RESET, all I/O ports are defined as input (inputs are at hi-impedance) since the I/O control registers (TRISA, TRISB, TRISC) are all set.

7.1 PORTA

PORTA is a 4-bit I/O Register. Only the low order 4 bits are used (RA<3:0>). Bits 7-4 are unimplemented and read as '0's.

7.2 PORTB

PORTB is an 8-bit I/O Register (PORTB<7:0>).

7.3 PORTC

PORTC is an 8-bit I/O Register for PIC16C55, PIC16C57 and PIC16CR57.

PORTC is a General Purpose Register for PIC16C54, PIC16CR54, PIC16C56, PIC16CR56, PIC16C58 and PIC16CR58.

7.4 TRIS Registers

The Output Driver Control Registers are loaded with the contents of the W Register by executing the `TRIS f` instruction. A '1' from a TRIS Register bit puts the corresponding output driver in a hi-impedance (input) mode. A '0' puts the contents of the output data latch on the selected pins, enabling the output buffer.

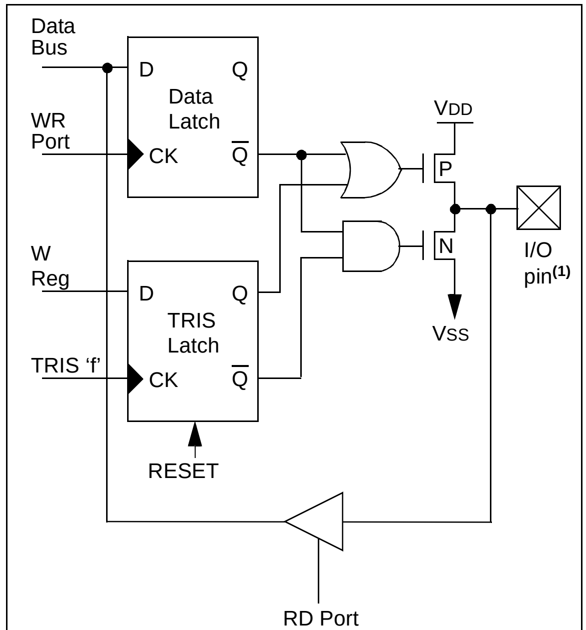
> **Note:** A read of the ports reads the pins, not the output data latches. That is, if an output driver on a pin is enabled and driven high, but the external system is holding it low, a read of the port will indicate that the pin is low.

The TRIS Registers are "write-only" and are set (output drivers disabled) upon RESET.

7.5 I/O Interfacing

The equivalent circuit for an I/O port pin is shown in Figure 7-1. All ports may be used for both input and output operation. For input operations these ports are non-latching. Any input must be present until read by an input instruction (e.g., `MOVF PORTB, W`). The outputs are latched and remain unchanged until the output latch is rewritten. To use a port pin as output, the corresponding direction control bit (in TRISA, TRISB, TRISC) must be cleared (= 0). For use as an input, the corresponding TRIS bit must be set. Any I/O pin can be programmed individually as input or output.

FIGURE 7-1: EQUIVALENT CIRCUIT FOR A SINGLE I/O PIN



Note 1: I/O pins have protection diodes to V_{DD} and V_{SS}.

TABLE 7-1: SUMMARY OF PORT REGISTERS

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value on Power-On Reset	Value on MCLR and WDT Reset
N/A	TRIS	I/O Control Registers (TRISA, TRISB, TRISC)								1111 1111	1111 1111
05h	PORTA	—	—	—	—	RA3	RA2	RA1	RA0	---- xxxx	---- uuuu
06h	PORTB	RB7	RB6	RB5	RB4	RB3	RB2	RB1	RB0	xxxx xxxx	uuuu uuuu
07h	PORTC	RC7	RC6	RC5	RC4	RC3	RC2	RC1	RC0	xxxx xxxx	uuuu uuuu

Legend: x = unknown, u = unchanged, — = unimplemented, read as '0', Shaded cells = unimplemented, read as '0'

NOTES:

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CALL — Subroutine Call

Syntax:	[*label*] CALL k
Operands:	0 ≤ k ≤ 255
Operation:	(PC) + 1→ TOS; k → PC<7:0>; (STATUS<6:5>) → PC<10:9>; 0 → PC<8>
Status Affected:	None
Encoding:	`1001` `kkkk` `kkkk`
Description:	Subroutine call. First, return address (PC+1) is pushed onto the stack. The eight bit immediate address is loaded into PC bits <7:0>. The upper bits PC<10:9> are loaded from STATUS<6:5>, PC<8> is cleared. `CALL` is a two-cycle instruction.
Words:	1
Cycles:	2
Example:	`HERE CALL THERE`

Before Instruction
PC = address `(HERE)`
After Instruction
PC = address `(THERE)`
TOS = address `(HERE + 1)`

CLRF — Clear f

Syntax:	[*label*] CLRF f
Operands:	0 ≤ f ≤ 31
Operation:	00h → (f); 1 → Z
Status Affected:	Z
Encoding:	`0000` `011f` `ffff`
Description:	The contents of register 'f' are cleared and the Z bit is set.
Words:	1
Cycles:	1
Example:	`CLRF FLAG_REG`

Before Instruction
FLAG_REG = 0x5A
After Instruction
FLAG_REG = 0x00
Z = 1

CLRW — Clear W

Syntax:	[*label*] CLRW
Operands:	None
Operation:	00h → (W); 1 → Z
Status Affected:	Z
Encoding:	`0000` `0100` `0000`
Description:	The W register is cleared. Zero bit (Z) is set.
Words:	1
Cycles:	1
Example:	`CLRW`

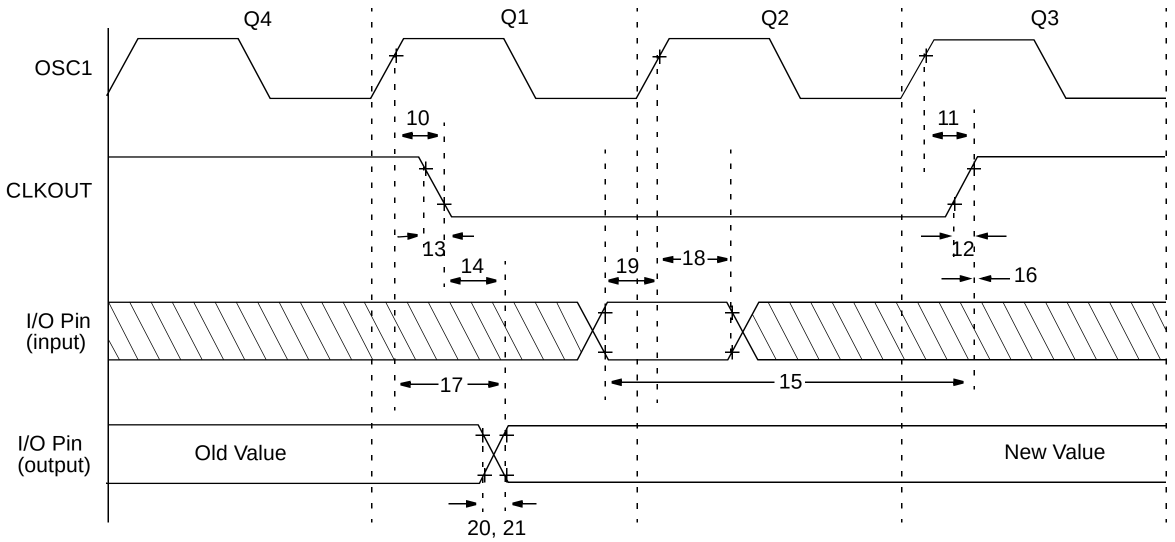
Before Instruction
W = 0x5A
After Instruction
W = 0x00
Z = 1

CLRWDT — Clear Watchdog Timer

Syntax:	[*label*] CLRWDT
Operands:	None
Operation:	00h → WDT; 0 → WDT prescaler (if assigned); 1 → $\overline{TO}$; 1 → $\overline{PD}$
Status Affected:	$\overline{TO}$, $\overline{PD}$
Encoding:	`0000` `0000` `0100`
Description:	The `CLRWDT` instruction resets the WDT. It also resets the prescaler, if the prescaler is assigned to the WDT and not Timer0. Status bits $\overline{TO}$ and $\overline{PD}$ are set.
Words:	1
Cycles:	1
Example:	`CLRWDT`

Before Instruction
WDT counter = ?
After Instruction
WDT counter = 0x00
WDT prescaler = 0
$\overline{TO}$ = 1
$\overline{PD}$ = 1

FIGURE 12-3: CLKOUT AND I/O TIMING - PIC16C54/55/56/57



Note: Please refer to Figure 12-1 for load conditions.

TABLE 12-2: CLKOUT AND I/O TIMING REQUIREMENTS - PIC16C54/55/56/57

AC Characteristics	Standard Operating Conditions (unless otherwise specified) Operating Temperature 0°C ≤ TA ≤ +70°C for commercial –40°C ≤ TA ≤ +85°C for industrial –40°C ≤ TA ≤ +125°C for extended					
Param No.	**Symbol**	**Characteristic**	**Min**	**Typ†**	**Max**	**Units**
10	TosH2ckL	OSC1↑ to CLKOUT↓(1)	—	15	30**	ns
11	TosH2ckH	OSC1↑ to CLKOUT↑(1)	—	15	30**	ns
12	TckR	CLKOUT rise time(1)	—	5.0	15**	ns
13	TckF	CLKOUT fall time(1)	—	5.0	15**	ns
14	TckL2ioV	CLKOUT↓ to Port out valid(1)	—	—	40**	ns
15	TioV2ckH	Port in valid before CLKOUT↑(1)	0.25 TCY+30*	—	—	ns
16	TckH2ioI	Port in hold after CLKOUT↑(1)	0*	—	—	ns
17	TosH2ioV	OSC1↑ (Q1 cycle) to Port out valid(2)	—	—	100*	ns
18	TosH2ioI	OSC1↑ (Q2 cycle) to Port input invalid (I/O in hold time)	TBD	—	—	ns
19	TioV2osH	Port input valid to OSC1↑ (I/O in setup time)	TBD	—	—	ns
20	TioR	Port output rise time(2)	—	10	25**	ns
21	TioF	Port output fall time(2)	—	10	25**	ns

* These parameters are characterized but not tested.

** These parameters are design targets and are not tested. No characterization data available at this time.

† Data in the Typical (“Typ”) column is at 5.0V, 25°C unless otherwise stated. These parameters are for design guidance only and are not tested.

Note 1: Measurements are taken in RC Mode where CLKOUT output is 4 x Tosc.

2: Please refer to Figure 12-1 for load conditions.

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13.0 ELECTRICAL CHARACTERISTICS - PIC16CR54A

Absolute Maximum Ratings[†]

Ambient Temperature under bias .... –55°C to +125°C
Storage Temperature .... –65°C to +150°C
Voltage on V_{DD} with respect to V_{SS} .... 0 to +7.5V
Voltage on $\overline{MCLR}$ with respect to V_{SS}[(1)] .... 0 to +14V
Voltage on all other pins with respect to V_{SS} .... –0.6V to (V_{DD} + 0.6V)
Total power dissipation[(2)] .... 800 mW
Max. current out of V_{SS} pin .... 150 mA
Max. current into V_{DD} pin .... 50 mA
Max. current into an input pin (T0CKI only) .... ±500 μA
Input clamp current, I_{IK} (VI < 0 or VI > V_{DD}) .... ±20 mA
Output clamp current, I_{OK} (V0 < 0 or V0 > V_{DD}) .... ±20 mA
Max. output current sunk by any I/O pin .... 25 mA
Max. output current sourced by any I/O pin .... 20 mA
Max. output current sourced by a single I/O port (PORTA or B) .... 40 mA
Max. output current sunk by a single I/O port (PORTA or B) .... 50 mA

Note 1: Voltage spikes below Vss at the $\overline{MCLR}$ pin, inducing currents greater than 80 mA may cause latch-up. Thus, a series resistor of 50 to 100 Ω should be used when applying a low level to the $\overline{MCLR}$ pin rather than pulling this pin directly to Vss.

2: Power Dissipation is calculated as follows: $P_{DIS} = V_{DD} \times \{I_{DD} - \sum I_{OH}\} + \sum \{(V_{DD}-V_{OH}) \times I_{OH}\} + \sum(V_{OL} \times I_{OL})$

† NOTICE: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

13.1 DC Characteristics: PIC16CR54A-04, 10, 20, PIC16LCR54A-04 (Commercial) PIC16CR54A-04I, 10I, 20I, PIC16LCR54A-04I (Industrial)

PIC16LCR54A-04 **PIC16LCR54A-04I** (Commercial, Industrial)	**Standard Operating Conditions (unless otherwise specified)** Operating Temperature $0°C \le T_A \le +70°C$ for commercial $-40°C \le T_A \le +85°C$ for industrial
PIC16CR54A-04, 10, 20 **PIC16CR54A-04I, 10I, 20I** (Commercial, Industrial)	**Standard Operating Conditions (unless otherwise specified)** Operating Temperature $0°C \le T_A \le +70°C$ for commercial $-40°C \le T_A \le +85°C$ for industrial

Param No.	Symbol	Characteristic/Device	Min	Typ†	Max	Units	Conditions
	IPD	**Power-down Current(2)**					
D006		PIC16LCR54A-Commercial	— — — —	1.0 2.0 3.0 5.0	6.0 8.0* 15 25	μA μA μA μA	VDD = 2.5V, WDT disabled VDD = 4.0V, WDT disabled VDD = 6.0V, WDT disabled VDD = 6.0V, WDT enabled
D006A		PIC16CR54A-Commercial	— — — —	1.0 2.0 3.0 5.0	6.0 8.0* 15 25	μA μA μA μA	VDD = 2.5V, WDT disabled VDD = 4.0V, WDT disabled VDD = 6.0V, WDT disabled VDD = 6.0V, WDT enabled
D007		PIC16LCR54A-Industrial	— — — — —	1.0 2.0 3.0 3.0 5.0	8.0 10* 20* 18 45	μA μA μA μA μA	VDD = 2.5V, WDT disabled VDD = 4.0V, WDT disabled VDD = 4.0V, WDT enabled VDD = 6.0V, WDT disabled VDD = 6.0V, WDT enabled
D007A		PIC16CR54A-Industrial	— — — — —	1.0 2.0 3.0 3.0 5.0	8.0 10* 20* 18 45	μA μA μA μA μA	VDD = 2.5V, WDT disabled VDD = 4.0V, WDT disabled VDD = 4.0V, WDT enabled VDD = 6.0V, WDT disabled VDD = 6.0V, WDT enabled

Legend: Rows with standard voltage device data only are shaded for improved readability.

* These parameters are characterized but not tested.

† Data in "Typ" column is at 5V, 25°C, unless otherwise stated. These parameters are for design guidance only, and are not tested.

Note 1: This is the limit to which VDD can be lowered in SLEEP mode without losing RAM data.

2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as bus loading, oscillator type, bus rate, internal code execution pattern and temperature also have an impact on the current consumption.

a) The test conditions for all IDD measurements in active Operation mode are: OSC1 = external square wave, from rail-to-rail; all I/O pins tristated, pulled to VSS, T0CKI = VDD, $\overline{\text{MCLR}}$ = VDD; WDT enabled/disabled as specified.

b) For standby current measurements, the conditions are the same, except that the device is in SLEEP mode. The power-down current in SLEEP mode does not depend on the oscillator type.

3: Does not include current through REXT. The current through the resistor can be estimated by the formula: IR = VDD/2REXT (mA) with REXT in kΩ.

13.2 DC Characteristics: PIC16CR54A-04E, 10E, 20E (Extended)

PIC16CR54A-04E, 10E, 20E (Extended)			**Standard Operating Conditions (unless otherwise specified)** Operating Temperature –40°C ≤ TA ≤ +125°C for extended				
Param No.	**Symbol**	**Characteristic**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
D001	VDD	**Supply Voltage** RC, XT and LP modes HS mode	 3.25 4.5	 — —	 6.0 5.5	 V V	
D002	VDR	**RAM Data Retention Voltage**(1)	—	1.5*	—	V	Device in SLEEP mode
D003	VPOR	**VDD Start Voltage** to ensure Power-on Reset	—	VSS	—	V	See Section 5.1 for details on Power-on Reset
D004	SVDD	**VDD Rise Rate** to ensure Power-on Reset	0.05*	—	—	V/ms	See Section 5.1 for details on Power-on Reset
D010	IDD	**Supply Current**(2) RC(3) and XT modes HS mode HS mode	 — — —	 1.8 4.8 9.0	 3.3 10 20	 mA mA mA	 FOSC = 4.0 MHz, VDD = 5.5V FOSC = 10 MHz, VDD = 5.5V FOSC = 16 MHz, VDD = 5.5V
D020	IPD	**Power-down Current**(2)	— —	5.0 0.8	22 18	μA μA	VDD = 3.25V, WDT enabled VDD = 3.25V, WDT disabled

* These parameters are characterized but not tested.

† Data in the Typical (“Typ”) column is based on characterization results at 25°C. This data is for design guidance only and is not tested.

Note 1: This is the limit to which VDD can be lowered in SLEEP mode without losing RAM data.

2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as bus loading, oscillator type, bus rate, internal code execution pattern and temperature also have an impact on the current consumption.

a) The test conditions for all IDD measurements in active Operation mode are: OSC1 = external square wave, from rail-to-rail; all I/O pins tristated, pulled to VSS, T0CKI = VDD, $\overline{\text{MCLR}}$ = VDD; WDT enabled/disabled as specified.

b) For standby current measurements, the conditions are the same, except that the device is in SLEEP mode.The power-down current in SLEEP mode does not depend on the oscillator type.

3: Does not include current through REXT. The current through the resistor can be estimated by the formula: IR = VDD/2REXT (mA) with REXT in kΩ.

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13.5 Timing Parameter Symbology and Load Conditions

The timing parameter symbols have been created with one of the following formats:

1. TppS2ppS
2. TppS

T	
F Frequency	T Time

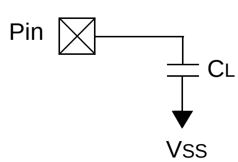
Lowercase letters (pp) and their meanings:

pp	
2 to	mc $\overline{MCLR}$
ck CLKOUT	osc oscillator
cy cycle time	os OSC1
drt device reset timer	t0 T0CKI
io I/O port	wdt watchdog timer

Uppercase letters and their meanings:

S	
F Fall	P Period
H High	R Rise
I Invalid (Hi-impedance)	V Valid
L Low	Z Hi-impedance

FIGURE 13-1: LOAD CONDITIONS FOR DEVICE TIMING SPECIFICATIONS - PIC16CR54A



C_L = 50 pF for all pins and OSC2 for RC modes

0 -15 pF for OSC2 in XT, HS or LP modes when external clock is used to drive OSC1

15.2 DC Characteristics: PIC16C54A-04E, 10E, 20E (Extended) PIC16LC54A-04E (Extended)

PIC16LC54A-04E (Extended)			**Standard Operating Conditions (unless otherwise specified)** Operating Temperature –40°C ≤ T_A ≤ +125°C for extended				
PIC16C54A-04E, 10E, 20E (Extended)			**Standard Operating Conditions (unless otherwise specified)** Operating Temperature –40°C ≤ T_A ≤ +125°C for extended				
Param No.	**Symbol**	**Characteristic**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
	I_{PD}	**Power-down Current(2)**					
D020		PIC16LC54A	—	2.5	15	μA	V_{DD} = 2.5V, WDT enabled, Extended
			—	0.25	7.0	μA	V_{DD} = 2.5V, WDT disabled, Extended
D020A		PIC16C54A	—	5.0	22	μA	V_{DD} = 3.5V, WDT enabled
			—	0.8	18*	μA	V_{DD} = 3.5V, WDT disabled

Legend: Rows with standard voltage device data only are shaded for improved readability.

* These parameters are characterized but not tested.

† Data in the Typical ("Typ") column is based on characterization results at 25°C. This data is for design guidance only and is not tested.

Note 1: This is the limit to which V_{DD} can be lowered in SLEEP mode without losing RAM data.

2: The supply current is mainly a function of the operating voltage and frequency. Other factors such as bus loading, oscillator type, bus rate, internal code execution pattern and temperature also have an impact on the current consumption.

a) The test conditions for all I_{DD} measurements in active Operation mode are: OSC1 = external square wave, from rail-to-rail; all I/O pins tristated, pulled to V_{SS}, T0CKI = V_{DD}, $\overline{MCLR}$ = V_{DD}; WDT enabled/disabled as specified.

b) For standby current measurements, the conditions are the same, except that the device is in SLEEP mode. The power-down current in SLEEP mode does not depend on the oscillator type.

3: Does not include current through R_{EXT}. The current through the resistor can be estimated by the formula: $I_R = V_{DD}/2R_{EXT}$ (mA) with R_{EXT} in kΩ.

NOTES:

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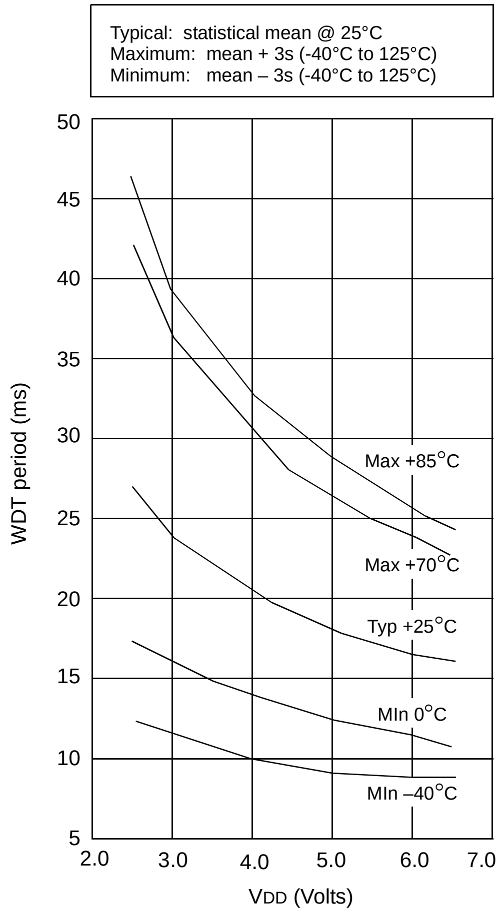
FIGURE 16-16: WDT TIMER TIME-OUT PERIOD vs. VDD(1)



Note 1: Prescaler set to 1:1.

FIGURE 16-17: TRANSCONDUCTANCE (gm) OF HS OSCILLATOR vs. VDD

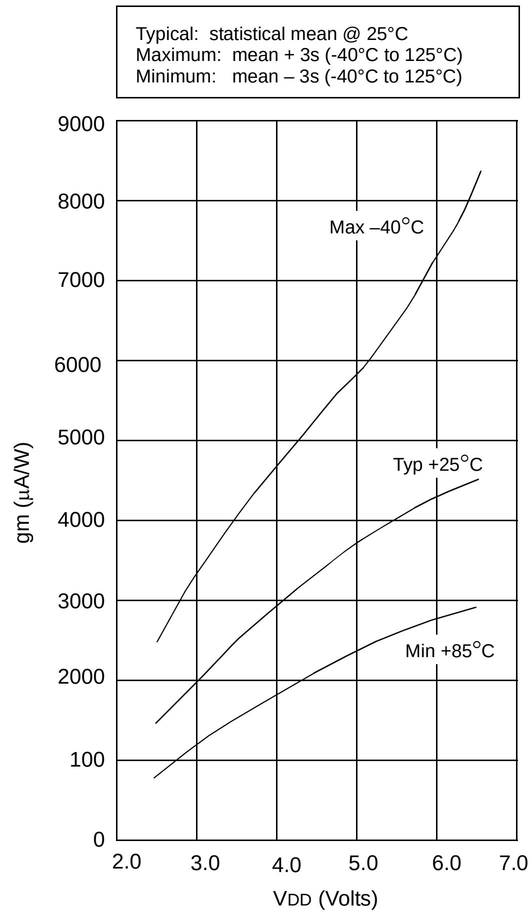


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FIGURE 18-12: TYPICAL IDD vs. FREQUENCY (WDT DISABLED, RC MODE @ 100 pF, 25°C)

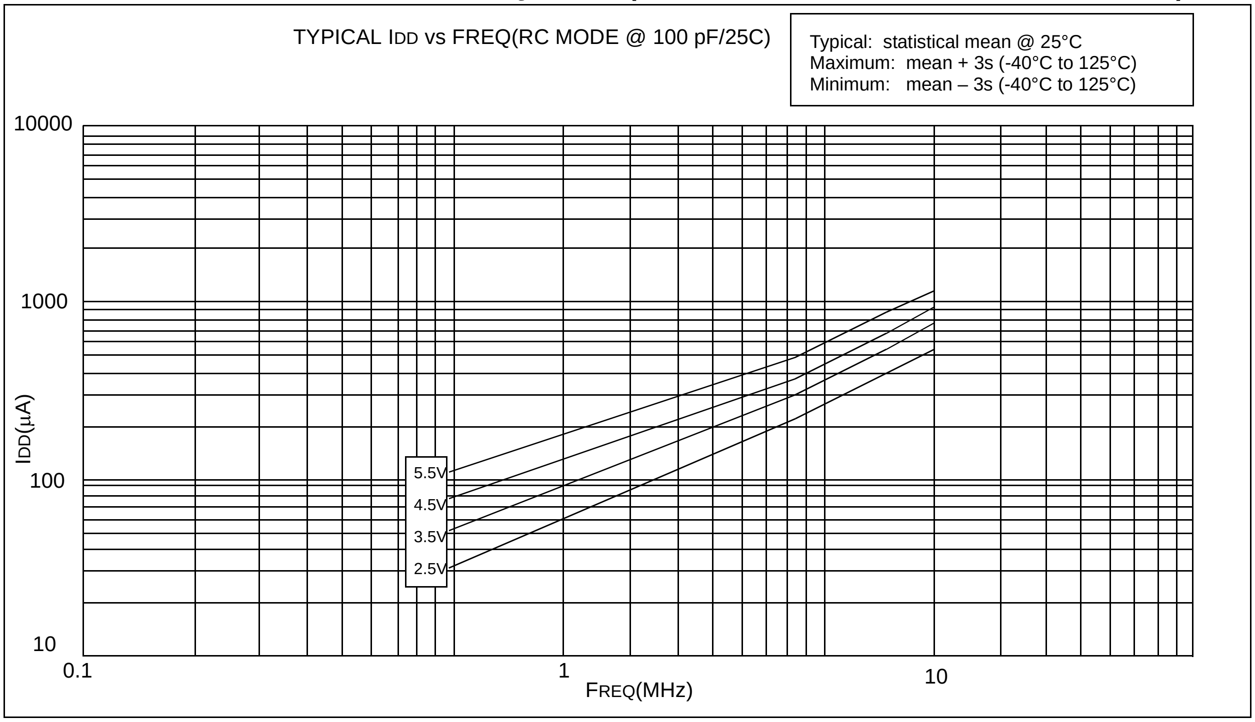
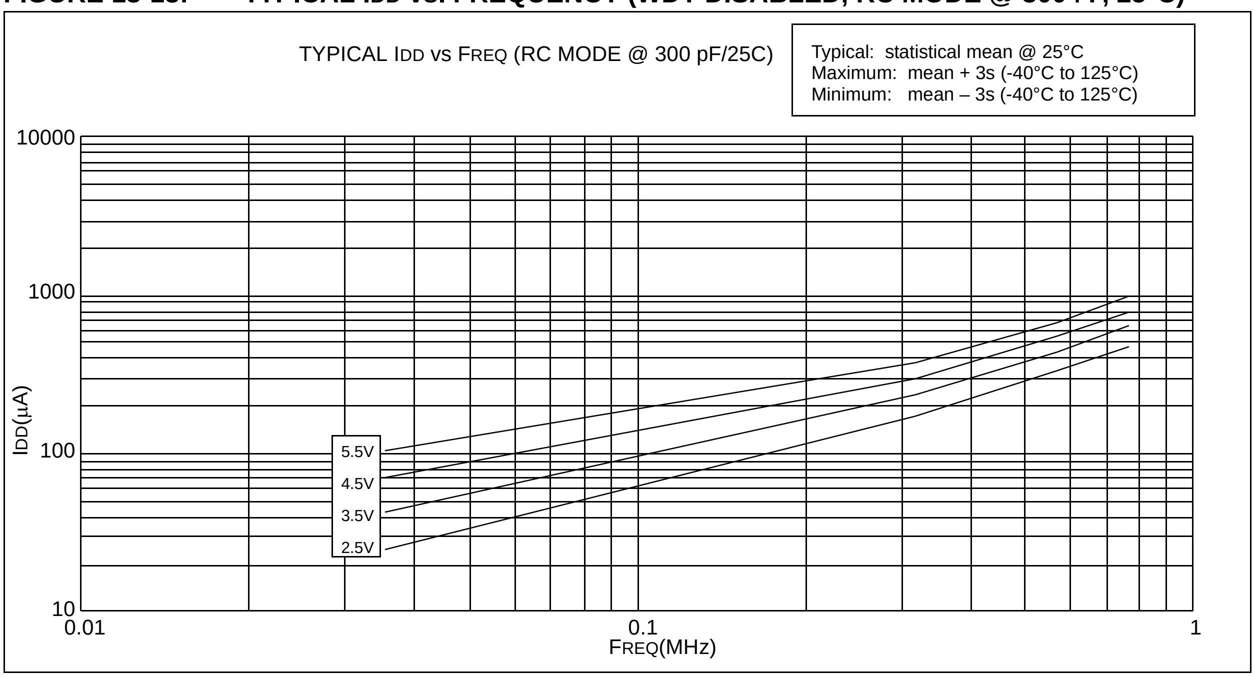


FIGURE 18-13: TYPICAL IDD vs. FREQUENCY (WDT DISABLED, RC MODE @ 300 pF, 25°C)



19.2 DC Characteristics: PIC16C54C/C55A/C56A/C57C/C58B-40 (Commercial)(1)

DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise specified) Operating Temperature 0°C ≤ TA ≤ +70°C for commercial				
Param No.	**Symbol**	**Characteristic**	**Min**	**Typ†**	**Max**	**Units**	**Conditions**
D030	V_{IL}	**Input Low Voltage**					
		I/O Ports	V_{SS}	—	0.8	V	4.5V <V_{DD} ≤ 5.5V
		$\overline{MCLR}$ (Schmitt Trigger)	V_{SS}	—	0.15 V_{DD}	V	
		T0CKI (Schmitt Trigger)	V_{SS}	—	0.15 V_{DD}	V	
		OSC1	V_{SS}	—	0.2 V_{DD}	V	HS, 20 MHz ≤ F_{OSC} ≤ 40 MHz
D040	V_{IH}	**Input High Voltage**					
		I/O ports	2.0	—	V_{DD}	V	4.5V < V_{DD} ≤ 5.5V
		$\overline{MCLR}$ (Schmitt Trigger)	0.85 V_{DD}	—	V_{DD}	V	
		T0CKI (Schmitt Trigger)	0.85 V_{DD}	—	V_{DD}	V	
		OSC1	0.8 V_{DD}	—	V_{DD}	V	HS, 20 MHz ≤ F_{OSC} ≤ 40 MHz
D050	V_{HYS}	**Hysteresis of Schmitt Trigger inputs**	0.15 V_{DD}*	—	—	V	
D060	I_{IL}	**Input Leakage Current(2,3)**					**For V_{DD} ≤ 5.5V:**
		I/O ports	-1.0	0.5	+1.0	μA	V_{SS} ≤ V_{PIN} ≤ V_{DD}, pin at hi-impedance
		$\overline{MCLR}$	-5.0	—	+5.0	μA	V_{PIN} = V_{SS} +0.25V
		$\overline{MCLR}$	—	0.5	+3.0	μA	V_{PIN} = V_{DD}
		T0CKI	-3.0	0.5	+3.0	μA	V_{SS} ≤ V_{PIN} ≤ V_{DD}
		OSC1	-3.0	0.5	—	μA	V_{SS} ≤ V_{PIN} ≤ V_{DD}, HS
D080	V_{OL}	**Output Low Voltage**					
		I/O ports	—	—	0.6	V	I_{OL} = 8.7 mA, V_{DD} = 4.5V
D090	V_{OH}	**Output High Voltage(3)**					
		I/O ports	V_{DD} - 0.7	—	—	V	I_{OH} = -5.4 mA, V_{DD} = 4.5V

* These parameters are characterized but not tested.

† Data in the Typical ("Typ") column is based on characterization results at 25°C. This data is for design guidance only and is not tested.

Note 1: Device operation between 20 MHz to 40 MHz requires the following: V_{DD} between 4.5V to 5.5V, OSC1 pin externally driven, OSC2 pin not connected and HS oscillator mode and commercial temperatures. For operation between DC and 20 MHz, See Section 17.3.

2: The leakage current on the $\overline{MCLR}$/V_{PP} pin is strongly dependent on the applied voltage level. The specified levels represent normal operating conditions. Higher leakage current may be measured at different input voltage.

3: Negative current is defined as coming out of the pin.

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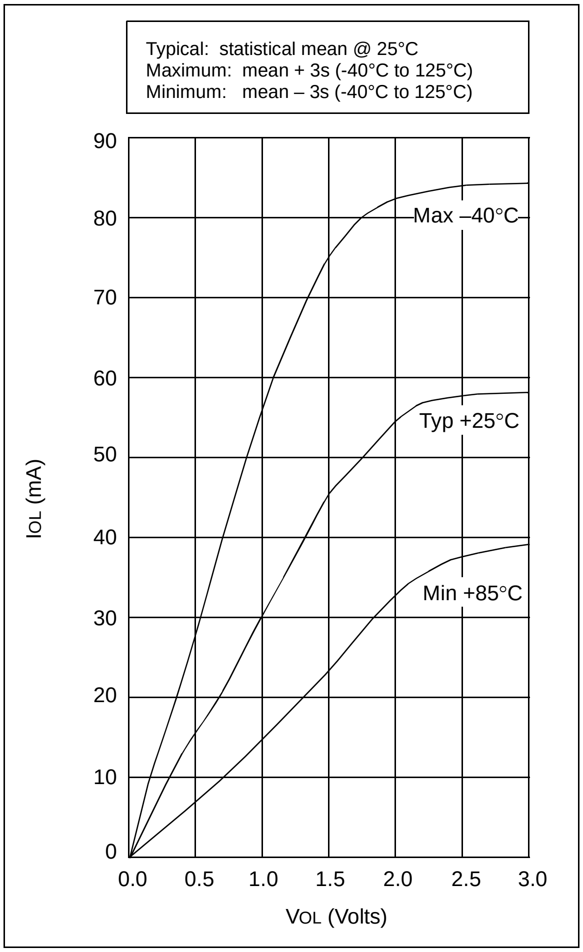
FIGURE 20-9: IOL VS. VOL, VDD = 5 V



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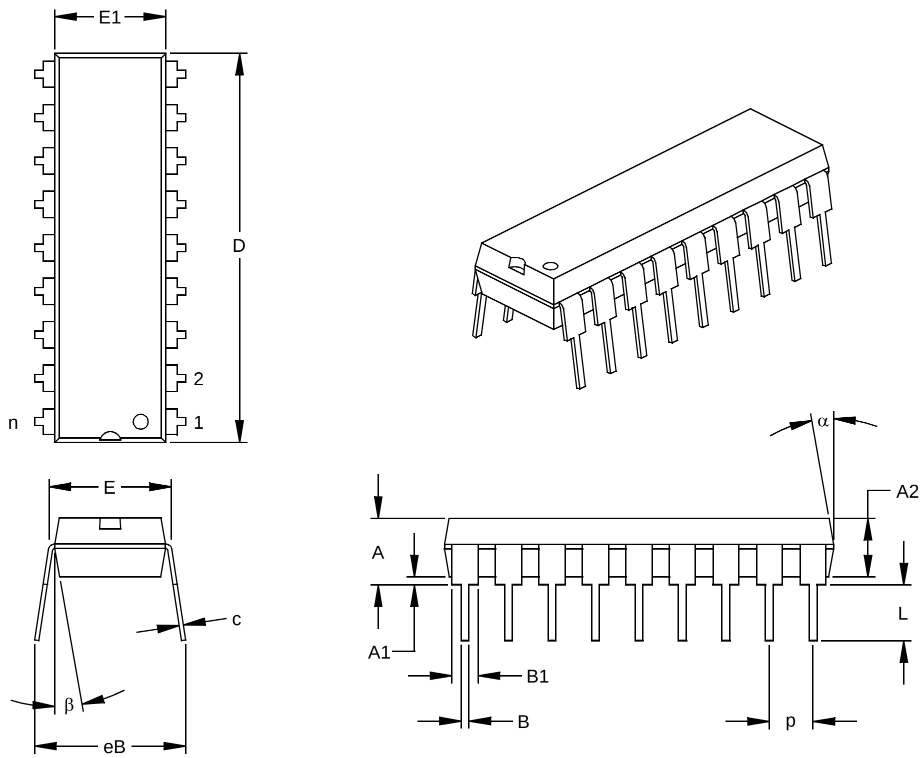
18-Lead Plastic Dual In-line (P) – 300 mil (PDIP)

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



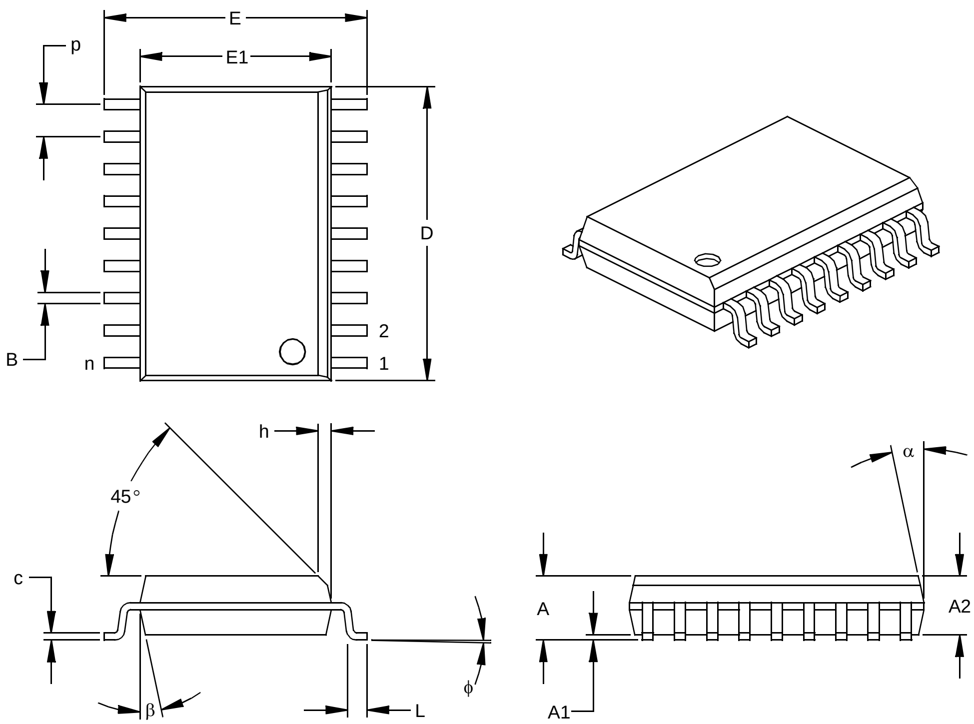
Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		18			18	
Pitch	p		.100			2.54	
Top to Seating Plane	A	.140	.155	.170	3.56	3.94	4.32
Molded Package Thickness	A2	.115	.130	.145	2.92	3.30	3.68
Base to Seating Plane	A1	.015			0.38		
Shoulder to Shoulder Width	E	.300	.313	.325	7.62	7.94	8.26
Molded Package Width	E1	.240	.250	.260	6.10	6.35	6.60
Overall Length	D	.890	.898	.905	22.61	22.80	22.99
Tip to Seating Plane	L	.125	.130	.135	3.18	3.30	3.43
Lead Thickness	c	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.058	.070	1.14	1.46	1.78
Lower Lead Width	B	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing §	eB	.310	.370	.430	7.87	9.40	10.92
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

* Controlling Parameter
§ Significant Characteristic

Notes:
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010” (0.254mm) per side.
JEDEC Equivalent: MS-001
Drawing No. C04-007

18-Lead Plastic Small Outline (SO) – Wide, 300 mil (SOIC)

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		18			18	
Pitch	p		.050			1.27	
Overall Height	A	.093	.099	.104	2.36	2.50	2.64
Molded Package Thickness	A2	.088	.091	.094	2.24	2.31	2.39
Standoff §	A1	.004	.008	.012	0.10	0.20	0.30
Overall Width	E	.394	.407	.420	10.01	10.34	10.67
Molded Package Width	E1	.291	.295	.299	7.39	7.49	7.59
Overall Length	D	.446	.454	.462	11.33	11.53	11.73
Chamfer Distance	h	.010	.020	.029	0.25	0.50	0.74
Foot Length	L	.016	.033	.050	0.41	0.84	1.27
Foot Angle	φ	0	4	8	0	4	8
Lead Thickness	c	.009	.011	.012	0.23	0.27	0.30
Lead Width	B	.014	.017	.020	0.36	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

* Controlling Parameter
§ Significant Characteristic

Notes:
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010” (0.254mm) per side.
JEDEC Equivalent: MS-013
Drawing No. C04-051

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APPENDIX A: COMPATIBILITY

To convert code written for PIC16CXX to PIC16C5X, the user should take the following steps:

1. Check any `CALL`, `GOTO` or instructions that modify the PC to determine if any program memory page select operations (PA2, PA1, PA0 bits) need to be made.
2. Revisit any computed jump operations (write to PC or add to PC, etc.) to make sure page bits are set properly under the new scheme.
3. Eliminate any special function register page switching. Redefine data variables to reallocate them.
4. Verify all writes to STATUS, OPTION, and FSR registers since these have changed.
5. Change RESET vector to proper value for processor used.
6. Remove any use of the `ADDLW`, `RETURN` and `SUBLW` instructions.
7. Rewrite any code segments that use interrupts.

APPENDIX B: REVISION HISTORY

Revision KE (January 2013)

Added a note to each package outline drawing.

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